

SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

# 2SC3258

HIGH CURRENT SWITCHING APPLICATIONS.

FEATURES:

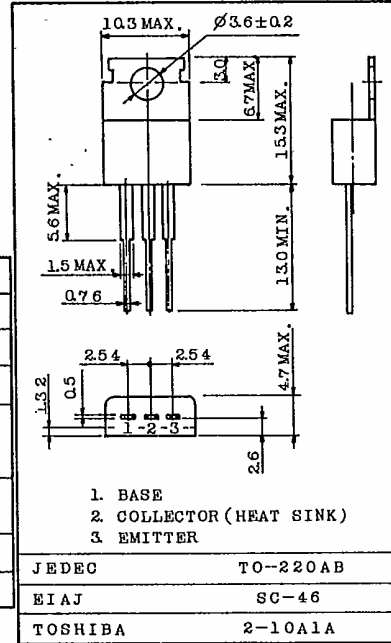
- Low Collector Saturation Voltage :  $V_{CE(sat)}=0.4V(\text{Max.})$  at  $I_C=3A$
- High Speed Switching Time :  $t_{stg}=1.0\mu s(\text{Typ.})$
- Complementary to 2SA1293.

MAXIMUM RATINGS ( $T_a=25^\circ C$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	100	V
Collector-Emitter Voltage	$V_{CEO}$	80	V
Emitter-Base Voltage	$V_{EBO}$	7	V
Collector Current	DC $I_C$	5	A
	Pulse $I_{CP}$	8	
Collector Power Dissipation ( $T_c=25^\circ C$ )	$P_C$	30	W
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	-55 ~ 150	$^\circ C$

INDUSTRIAL APPLICATIONS

Unit in mm



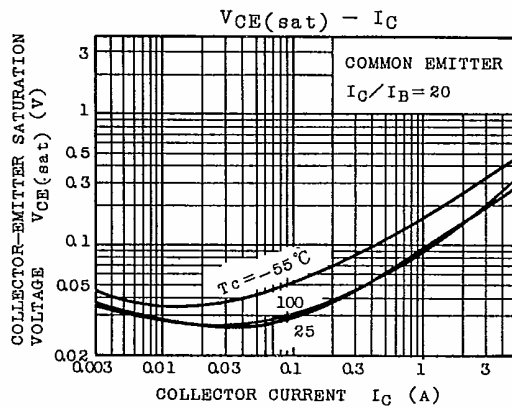
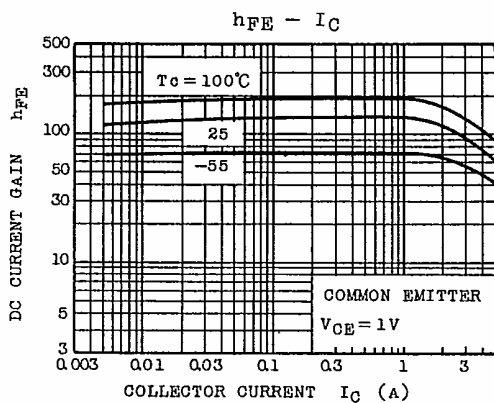
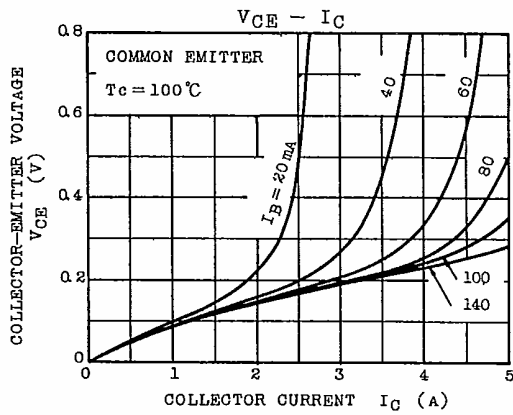
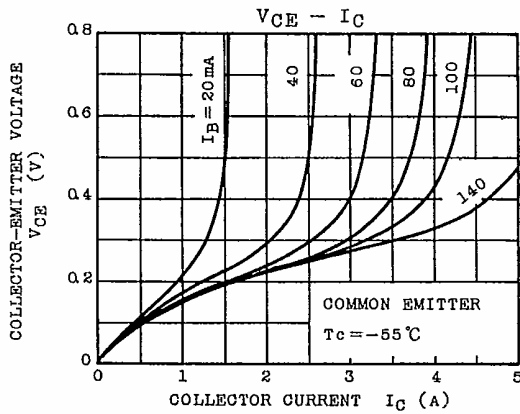
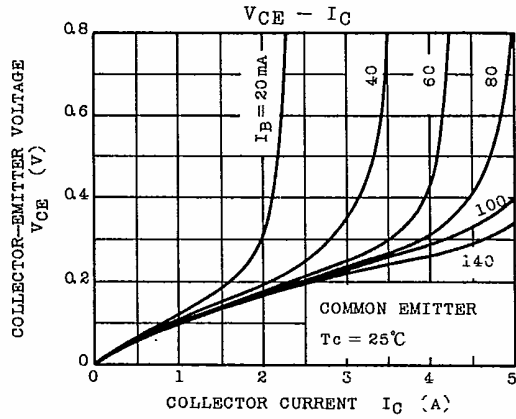
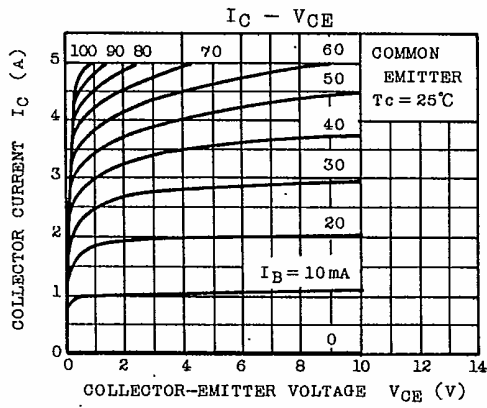
ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ C$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB}=100V, I_E=0$	-	-	1	$\mu A$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=7V, I_C=0$	-	-	1	$\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	80	-	-	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE}=1V, I_C=1A$	70	-	240	
	$h_{FE(2)}$	$V_{CE}=1V, I_C=3A$	40	-	-	
Saturation Voltage	Collector-Emitter $V_{CE(sat)}$	$I_C=3A, I_B=0.15A$	-	0.2	0.4	V
	Base-Emitter $V_{BE(sat)}$		-	0.9	1.2	
Transition Frequency	$f_T$	$V_{CE}=4V, I_C=1A$	-	120	-	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=10V, I_E=0, f=1MHz$	-	80	-	pF
Switching Time	Turn-on Time $t_{on}$		-	0.2	-	$\mu s$
	Storage Time $t_{stg}$		-	1.0	-	
	Fall Time $t_f$		-	0.1	-	

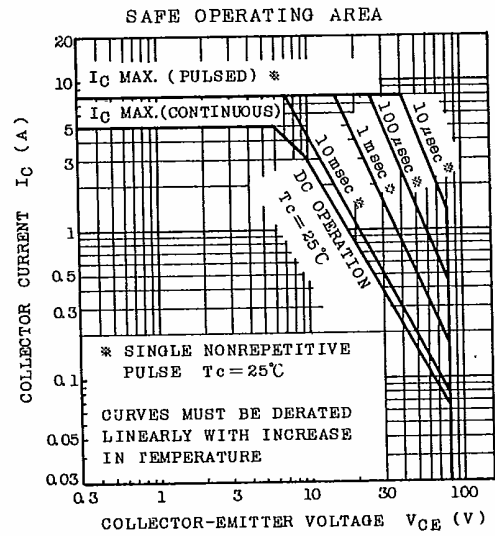
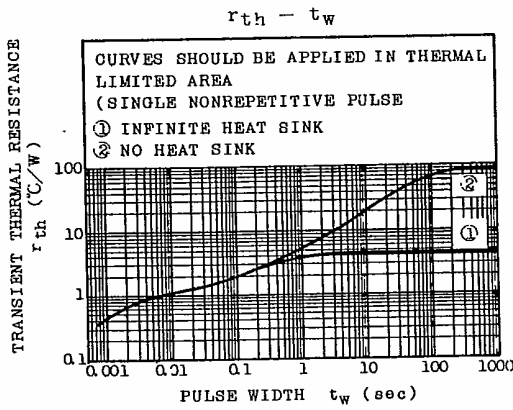
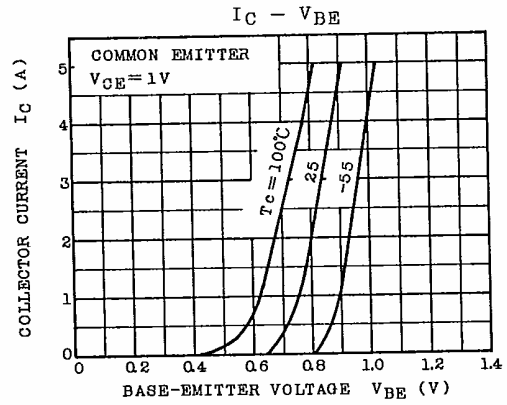
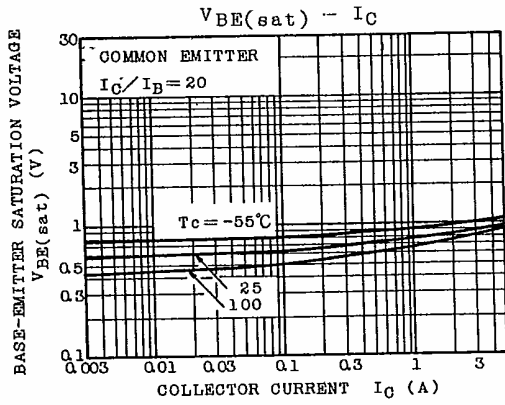
Note :  $h_{FE(1)}$  Classification O : 70~140, Y : 120~240

TOSHIBA CORPORATION

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TOSHIBA CORPORATION



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Datasheets for electronic components.